



IXFN80N50Q3 Information



For Reference Only

Part Number IXFN80N50Q3

Manufacturer IXYS

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 500V 63A SOT-227

Package SOT-227-4, miniBLOC

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IXFN80N50Q3 Specifications

Manufacturer Part Number Manufacturer IXYS Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single SOT-227-4, miniBLOC Series HiPerFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Least Connections of (Gigs) (Max) @ Vds		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single SOT-227-4, miniBLOC Series HiPerFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single SOT-227-4, miniBLOC HiPerFET? N-Channel MOSFET (Metal Oxide) 500V 63A Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 6.5V @ 8mA Gate Charge (Qg) (Max) @ Vgs	Manufacturer Part Number	IXFN80N50Q3
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Series HiPerFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 500V Current - Continuous Drain (Id) @ 25°C 63A Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 6.5V @ 8mA Gate Charge (Qg) (Max) @ Vgs 200nC @ 10V		Transistors - FETs, MOSFETs - Single
FET Type Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 63A Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs N-Channel NOSFET (Metal Oxide) 500V 63A 10V 200r @ 8mA	Package	SOT-227-4, miniBLOC
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 63A Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs MOSFET (Metal Oxide) 500V 63A 10V 200r @ 8mA	Series	HiPerFET?
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 63A Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 500V 63A 10V 200r 200	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C 63A Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 6.5V @ 8mA Gate Charge (Qg) (Max) @ Vgs 200nC @ 10V	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 10V 6.5V @ 8mA 200nC @ 10V	Drain to Source Voltage (Vdss)	500V
Vgs(th) (Max) @ Id 6.5V @ 8mA Gate Charge (Qg) (Max) @ Vgs 200nC @ 10V	Current - Continuous Drain (Id) @ 25°C	63A
Gate Charge (Qg) (Max) @ Vgs 200nC @ 10V	Drive Voltage (Max Rds On, Min Rds On)	10V
	Vgs(th) (Max) @ Id	6.5V @ 8mA
Imput Conscitones (Ciss) (May) @ VIIs	Gate Charge (Qg) (Max) @ Vgs	200nC @ 10V
input Capacitance (Ciss) (Max) @ Vus	Input Capacitance (Ciss) (Max) @ Vds	10000pF @ 25V
Vgs (Max) ±30V	Vgs (Max)	±30V
FET Feature -	FET Feature	-
Power Dissipation (Max) 780W (Tc)	Power Dissipation (Max)	780W (Tc)
Rds On (Max) @ Id, Vgs 65 mOhm @ 40A, 10V	Rds On (Max) @ Id, Vgs	65 mOhm @ 40A, 10V
Operating Temperature $-55^{\circ}\text{C} \sim 150^{\circ}\text{C} \text{ (TJ)}$	Operating Temperature	-55°C ~ 150°C (TJ)
Mounting Type Chassis Mount	Mounting Type	Chassis Mount
Supplier Device Package SOT-227B	Supplier Device Package	SOT-227B
Package / Case SOT-227-4, miniBLOC	Package / Case	SOT-227-4, miniBLOC
Report error		Report errors?

IXFN80N50Q3 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IXFN80N50Q3 Payment Methods



















IXFN80N50Q3 Shipping Methods













If you have any question about IXFN80N50Q3, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com